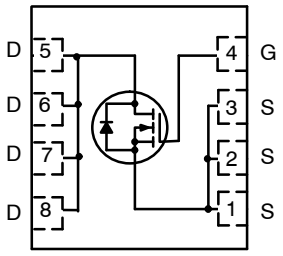
MOSFET – N-Channel, UltraFET Trench

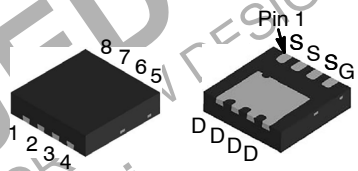
220 V, 7.0 A, 366 mΩ

FDMC2674

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
220 V	366 mΩ @ 10 V	7.0 A



N-CHANNEL MOSFET



WDFN8 3.3 × 3.3, 0.65P
CASE 511DH

General Description

UltraFET device combines characteristics that enable benchmark efficiency in power conversion applications. Optimized for $R_{DS(on)}$, low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

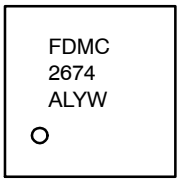
Features

- Max $R_{DS(on)}$ = 366 mΩ at V_{GS} = 10 V, I_D = 1.0 A
- Typ Q_g = 12.7 nC at V_{GS} = 10 V
- Low Miller Charge
- Low Q_{rr} Body Diode
- Optimized Efficiency at High Frequencies
- UIS Capability (Single Pulse and Repetitive Pulse)
- Pb−Free, Halide Free and RoHS Compliant

Applications

- DC−DC Converters and Off−Line UPS
- Distributed Power Architectures

MARKING DIAGRAM



FDMC2674 = Specific Device Code
A = Assembly Site
L = Wafer Lot Number
YW = Assembly Start Week

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain to Source Voltage	220	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current: Continuous (Silicon limited) T_C = 25°C Continuous (Note 1b) T_A = 25°C Pulsed	 7.0 1.0 13.8	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	11	mJ
P_D	Power Dissipation: T_C = 25°C T_A = 25°C (Note 1a)	 42 2.1	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	60	

ORDERING INFORMATION

Device	Package	Shipping†
FDMC2674	WDFN8 (Pb−Free, Halide Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

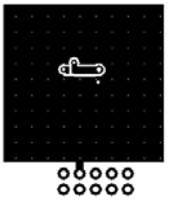
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	220	–	–	V
ΔBV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C	–	248	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 176 V, V_{GS} = 0 V	–	–	1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2	3.4	4	V
$\Delta V_{GS(th)}$ /ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C	–	–10.2	–	mV/°C
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 1.0 A	–	305	366	mΩ
		V_{GS} = 10 V, I_D = 1.0 A, T_J = 150°C	–	678	814	
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 100 V, V_{GS} = 0 V, f = 1 MHz	–	880	1180	pF
C_{oss}	Output Capacitance		–	70	95	pF
C_{rss}	Reverse Transfer Capacitance		–	11	20	pF
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 100 V, I_D = 1.0 A, V_{GS} = 10 V, R_{GEN} = 2.4 Ω	–	9	18	ns
t_r	Rise Time		–	13	23	ns
$t_{d(off)}$	Turn-Off Delay Time		–	15	27	ns
t_f	Fall Time		–	21	34	ns
$Q_{g(TOT)}$	Total Gate Charge at 10 V	V_{GS} = 0 V to 10 V, V_{DD} = 15 V, I_D = 1.0 A	–	12.7	18	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 15 V, I_D = 1.0 A	–	3.8	–	nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 15 V, I_D = 1.0 A	–	2.9	–	nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.2 A (Note 2)	–	0.8	1.5	V
t_{rr}	Reverse Recovery Time	I_F = 1.0 A, di/dt = 100 A/μs	–	–	60	ns
Q_{rr}	Reverse Recovery Charge		–	–	109	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 oz copper pad on a 1.5 × 1.5 in. board of FR−4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user’s board design.
   (a) $R_{\theta JA}$ = 60°C/W when mounted on a 1 in^2 pad of 2 oz copper, 1.5’ × 1.5’ × 0.062’ thick PCB.
   (b) $R_{\theta JA}$ = 135°C/W when mounted on a minimum pad of 2 oz copper.



a) 60°C/W when mounted on a 1 in^2 pad of 2 oz copper.

b) 135°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Starting T_J = 25°C; N-ch: L = 1 mH, I_{AS} = 4.7 A, V_{DD} = 25 V, V_{GS} = 10 V.

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

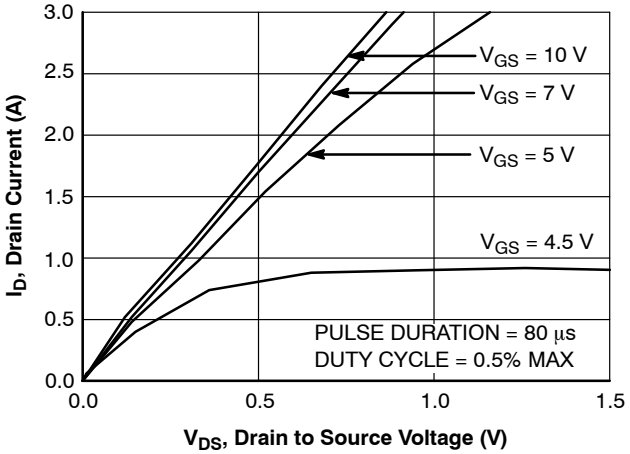


Figure 1. On−Region Characteristics

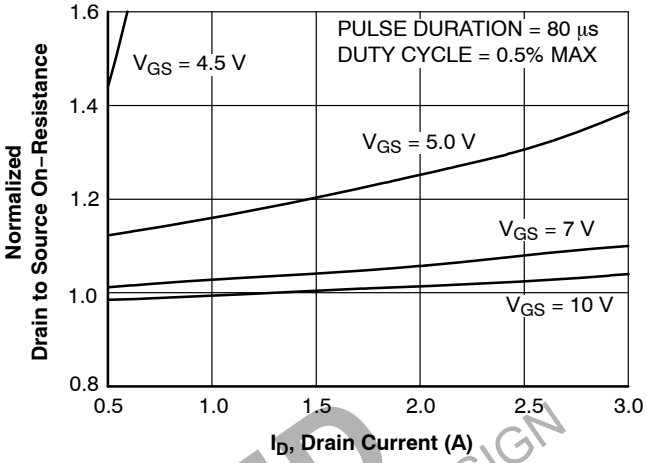


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

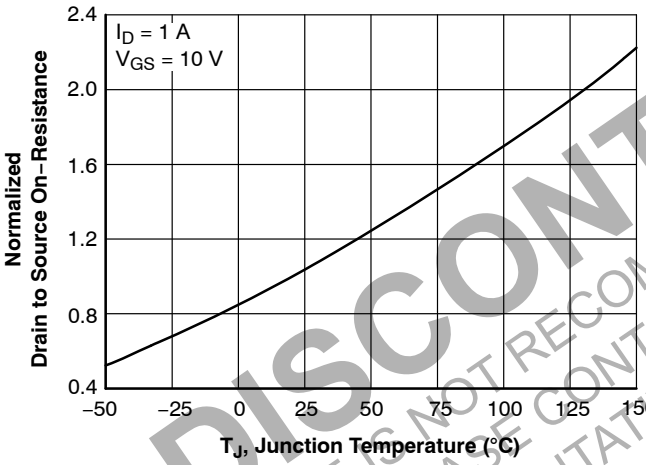


Figure 3. Normalized On−Resistance vs. Junction Temperature

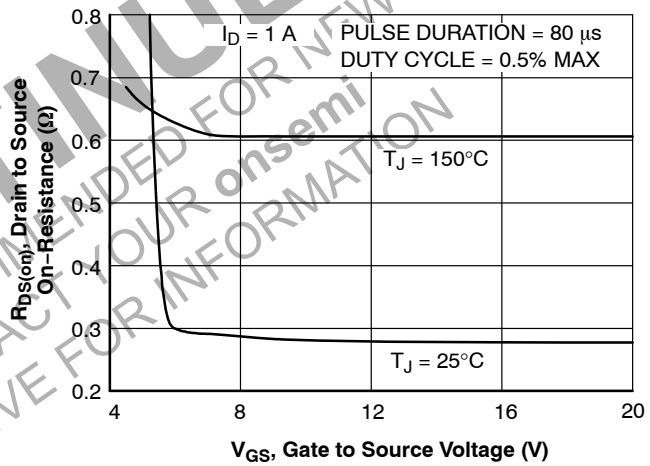


Figure 4. On−Resistance vs. Gate to Source Voltage

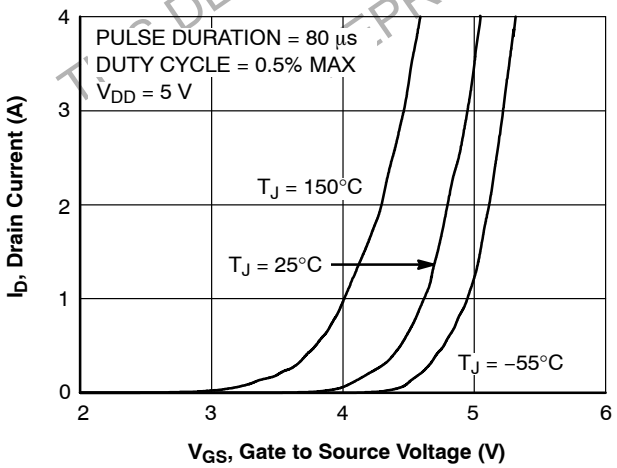


Figure 5. Transfer Characteristics

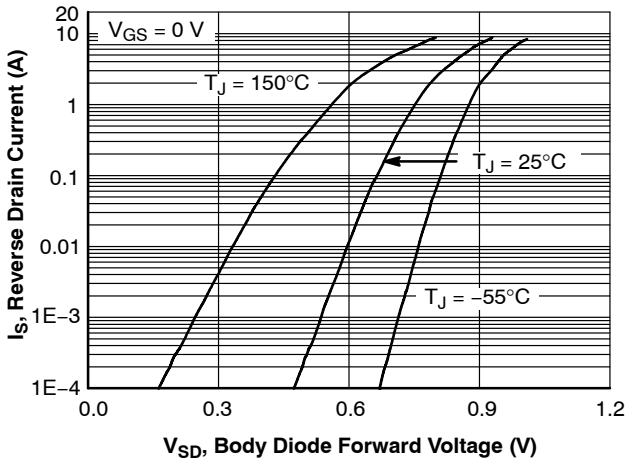


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (continued)

(T_J = 25°C unless otherwise noted)

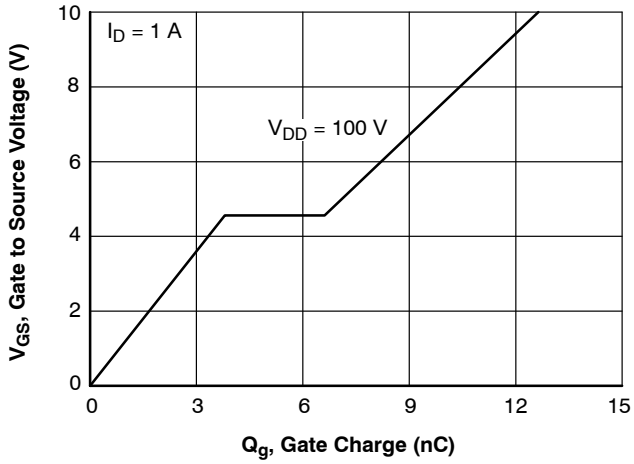


Figure 7. Gate Charge Characteristics

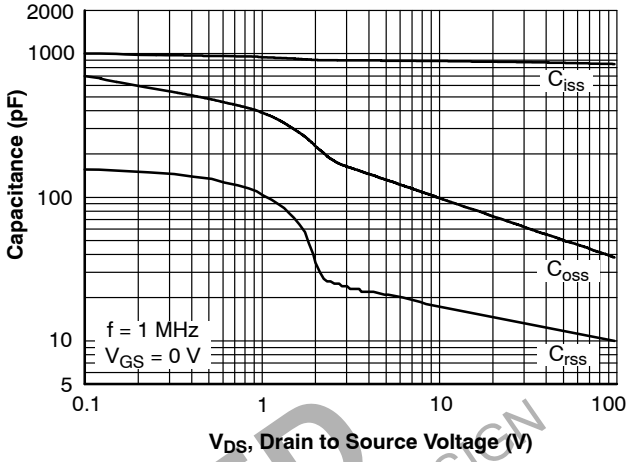


Figure 8. Capacitance vs. Drain to Source Voltage

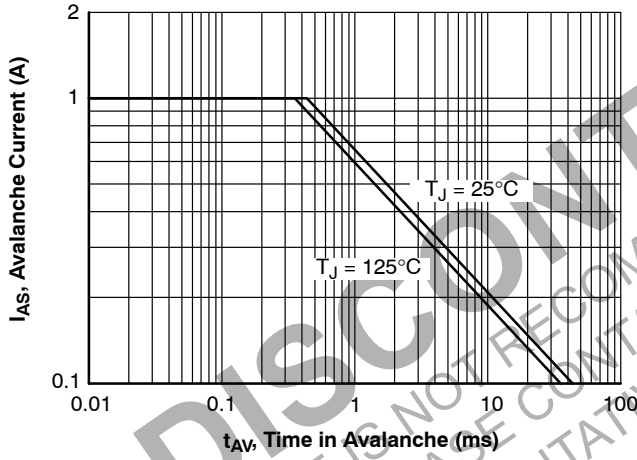


Figure 9. Unclamped Inductive Switching Capability

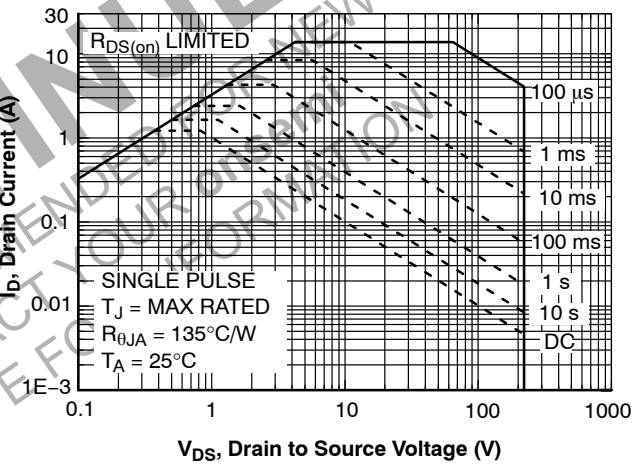


Figure 10. Forward Bias Safe Operating Area

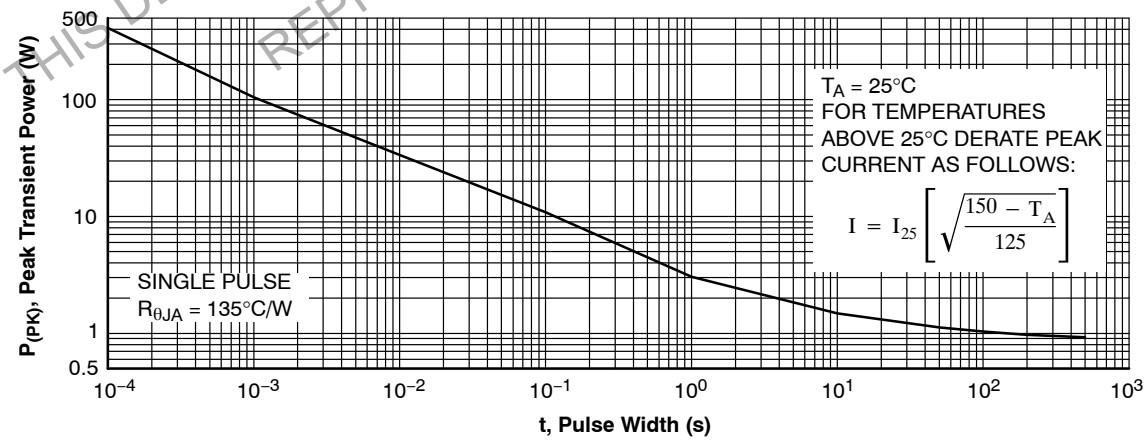


Figure 11. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (continued)

(T_J = 25°C unless otherwise noted)

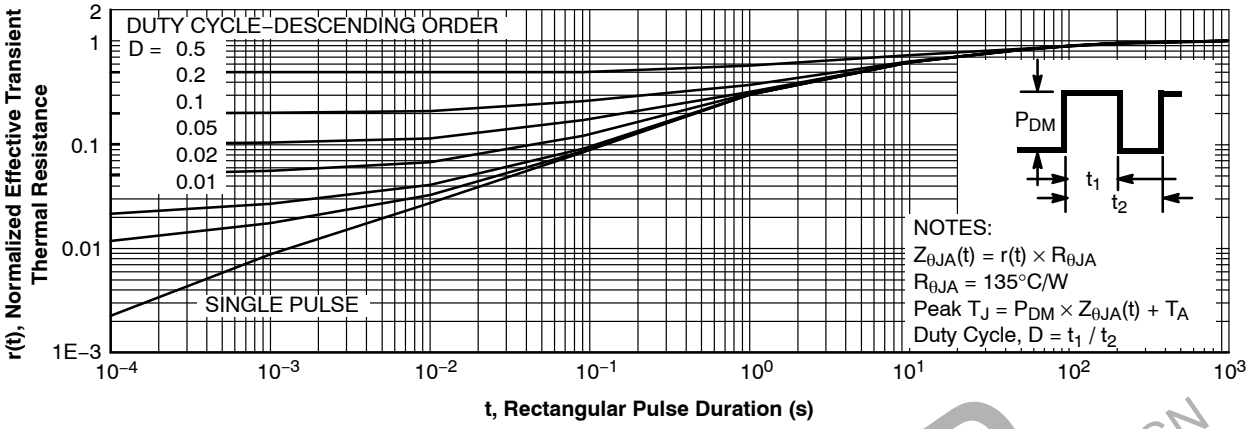
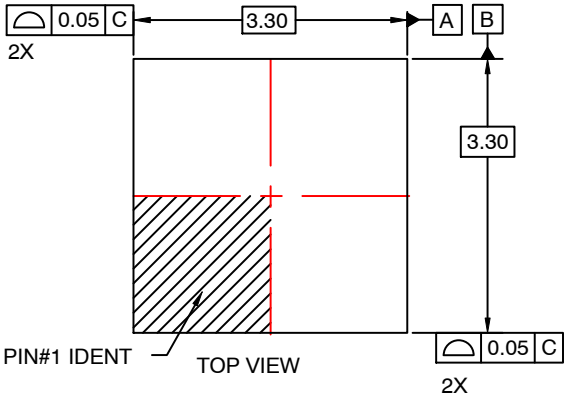
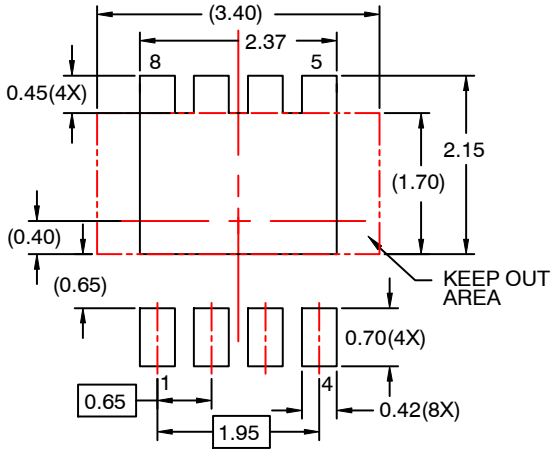


Figure 12. Transient Thermal Response Curve

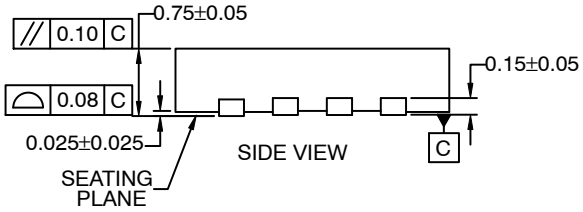
WDFN8 3.3x3.3, 0.65P
CASE 511DH
ISSUE O

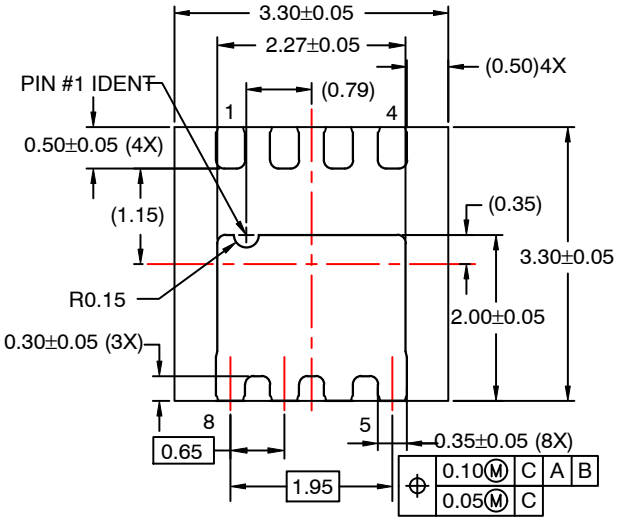
DATE 31 JUL 2016





RECOMMENDED LAND PATTERN





BOTTOM VIEW

NOTES:

A. DOES NOT CONFORM TO JEDEC REGISTRATION MO−229

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

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